

# BG3 SERIES CLIENT SSD

The BG3 series leverages 64-layer, 3-bit-per-cell (TLC) BiCS FLASH<sup>™</sup> and features NVMe<sup>™</sup> Revision 1.2.1. With Host Memory Buffer (HMB) technology, this SSD series retains high performance in a DRAM-less architecture, while enabling reduced power and a smaller footprint.

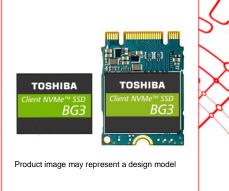
BG3 SSDs, as an innovative, next generation single-package ball grid array (BGA) SSD product line, harness the flexibility in system design that enables mobile computing and IoT embedded devices to be smaller, lighter, faster, and more power efficient. Also, these power-saving BG3 SSDs offer data center applications an alternative solution for server boot storage.

The BG3 series is available in 128GB, 256GB, and 512GB capacities. All three models are available in a surface-mount single package M.2 1620 or a removable module M.2 2230 form factor. BG3 SED models are also available.

#### > KEY FEATURES

- Toshiba 64-Layer BiCS FLASH™
- PCIe<sup>®</sup> Gen3\*2L NVMe<sup>™</sup>
- Capacities up to 512GB
- M.2 1620 single package and M.2 2230 single-sided form factor
- TCG OPAL 2.01 Optional for SED

# SSD



### > APPLICATIONS

- Ultra-mobile PCs
- 2-in-1 notebook PCs
- IoT/embedded devices
- Server and storage array boot drives

### > SPECIFICATIONS

Standard Models			520-S2 Package	M.2 1620-S3 Single Package		230-S2 -sided	M.2 2230-S3 Single-sided
Model	(Non-SED)	KBG30ZPZ128G	KBG30ZPZ256G	KBG30ZPZ512G	KBG30ZMS128G	KBG30ZMS256G	KBG30ZMS512G
Number	(SED)	KBG3AZPZ128G	KBG3AZPZ256G	KBG3AZPZ512G	KBG3AZMS128G	KBG3AZMS256G	KBG3AZMS512G
Memory				TLC (BiCS	FLASH™)		
Interface			PCI Expre	ess <sup>®</sup> Base Specifica	ation Revision 3.1a	a (PCIe <sup>®</sup> )	
Maximum S	peed			16 GT/s (PCle <sup>®</sup>	Gen3x2 Lane)		
Command			N	VM Express <sup>™</sup> Revis	sion 1.2.1 (NVMe <sup>T</sup>	<sup>-M</sup> )	
Connector Type			-			M.2 B-M	
Formatted C	apacity <sup>1)</sup>	128 GB	256 GB	512 GB	128 GB	256 GB	512 GB
Perfor-	Sequential Read	1,310 MB/s {1,250 MiB/s}	1,415 MB/s {1,350 MiB/s}	1,520 MB/s {1,450 MiB/s}	1,310 MB/s {1,250 MiB/s}	1,415 MB/s {1,350 MiB/s}	1,520 MB/s {1,450 MiB/s}
mance <sup>2)</sup> (Up to)	Sequential Write	470 MB/s {450 MiB/s}	840 MB/s {800 MiB/s}	1,050 MB/s {1,000 MiB/s}	470 MB/s {450 MiB/s}	840 MB/s {800 MiB/s}	1,050 MB/s {1,000 MiB/s}
Supply Voltage			3.3 V ±5 % 1.8 V ±5 % 1.2 V ±5 %			$3.3$ V $\pm 5$ %	
Power	Active	2.7 W typ.	2.8	N typ.	3.2 W typ.	3.3 V	V typ.
Consump- tion	L1.2 mode		5 mW typ.		5 mW typ.		
Size	Size		mm x mm x mm	20.0 mm x 16.0 mm x 1.5 mm	22.0	mm x mm x • mm	30.0 mm x 22.0 mm x 2.38 mm
Weight		0.85	g typ.	1.00 g typ.	2.42	g typ.	2.60 g typ.

Standard Models		M.2 1620-S2 Single Package	M.2 1620-S3 Single Package	M.2 2230-S2 Single-sided	M.2 2230-S3 Single-sided	
Tempera-		0 to 80 °C (Package Surface Tem	nperature)	0 to 80 °C (Components Temperature)		
ture	Non- operating	-40 to 85 °C				
Reliability <sup>3)</sup>		Mean Time to Failure (MTTF): 1,500,000 hours Product Life: Approximately 5 years				
More Features		<ul> <li>Device Self-test is supported.</li> <li>Host Controlled Thermal Mana</li> <li>The feature of Host Memory E</li> <li>Firmware security feature (online)</li> </ul>	Buffer (HMB) is supp	•••	ed.	
Compliance	e <sup>4)</sup>			, ISED, VCCI, Moroccan conformit		

- Note: 1) Definition of capacity: Toshiba Memory Corporation defines a megabyte (MB) as 1,000,000 bytes, a gigabyte (GB) as 1,000,000,000 bytes and a terabyte (TB) as 1,000,000,000 bytes. A computer operating system, however, reports storage capacity using powers of 2 for the definition of 1GB = 2<sup>30</sup> = 1,073,741,824 bytes and therefore shows less storage capacity. Available storage capacity (including examples of various media files) will vary based on file size, formatting, settings, software and operating system, such as Microsoft Operating System and/or pre-installed software applications, or media content. Actual formatted capacity may vary.
  - 2) Read and write speed, tested on the state of "Host Memory Buffer (HMB) = On", may vary depending on the host device, read and write conditions, and file size.
     1 MiP (mathibute) = 2<sup>20</sup> butes = 1.040 570 butes
    - 1 MiB (mebibyte) =  $2^{20}$  bytes = 1,048,576 bytes, and 1 MB (megabyte) = 1,000,000 bytes.
  - 3) MTTF (Mean Time to Failure) is not a guarantee or estimate of product life; it is a statistical value related to mean failure rates for a large number of products which may not accurately reflect actual operation. Actual operating life of the product may be different from the MTTF.
  - 4) The Safety/EMI Standard is supported for KBG3xZMSxxxx only.
- \* PCIe and PCI Express are registered trademarks of PCI-SIG
- \* NVMe<sup>™</sup> and NVM Express<sup>™</sup> are trademarks of NVM Express, Inc.
- \* All other company names, product names, and service names mentioned herein may be trademarks of their respective companies.
- \* Availability of the SED model line-up may vary by region.

### > ORDERING INFORMATION

<u>K</u> 1	$\frac{XX}{2}$ $\frac{X}{3}$	<u>X</u> 4	<u>X</u> 5	<u>X</u> 6	<u>X</u> 7	XXXX 8
1.	Product N	lame				K: SSD product
2.	Prodct Ca	ategoi	ry			BG: BG Series
3.	Developm	nent C	Gene	erati	on	3: Generation 3
4.	Option Co	ode 1				0: Non-SED
						A: SED
5.	Option Co	ode 2				Z: No-option
6. Connector Type					M: M.2 (B-M Key)	
			P: M.2 BGA			
7.	Form Fac	tor				S: M.2 2230 Single Sided
						Z: M.2 1620 Single Package
8.	8. Capacity			128G / 256G /512G		
						128G is 128 GB, 256G is 256 GB and 512G is 512 GB (1 GB = 1,000,000,000 bytes)

### > PRODUCT LINE UP

Model Number	Formatted Capacity	Form Factor/Connect Type	Function Note
KBG30ZPZ128G	128 GB		
KBG30ZPZ256G	256 GB	M.2 1620-S2 <sup>1)</sup>	Non-SED
KBG30ZPZ512G	512 GB	M.2 1620-S3 <sup>2)</sup>	
KBG3AZPZ128G	128 GB		
KBG3AZPZ256G	256 GB	M.2 1620-S2 <sup>1)</sup>	SED <sup>3)</sup>
KBG3AZPZ512G	512 GB	M.2 1620-S3 <sup>2)</sup>	
KBG30ZMS128G	128 GB		
KBG30ZMS256G	256 GB	M.2 2230-S2 <sup>1)</sup> -B-M	Non-SED
KBG30ZMS512G	512 GB	M.2 2230-S3 <sup>2)</sup> -B-M	•
KBG3AZMS128G	128 GB		
KBG3AZMS256G	256 GB	M.2 2230-S2 <sup>1)</sup> -B-M	SED <sup>3)</sup>
KBG3AZMS512G	512 GB	M.2 2230-S3 <sup>2)</sup> -B-M	

Note: 1) Single Sided/Top side 1.35mm Maximum Thickness

2) Single Sided/Top side 1.5 mm Maximum Thickness

3) Availability of the SED model line-up may vary by region.

# > CAPACITY

Conscitu	Total Number of User Addressable Sectors in LBA Mode			
Capacity	512 bytes sector	4,096 bytes sector		
128 GB <sup>1)</sup>	250,069,680	31,258,710		
256 GB <sup>1)</sup>	500,118,192	62,514,774		
512 GB <sup>1)</sup>	1,000,215,216	125,026,902		

Note: 1) 1 GB (Gigabyte) = 1,000,000,000 bytes

## > PERFORMANCE

Standard Models	KBG30ZPZ128G	KBG30ZPZ256G	KBG30ZPZ512G
	KBG3AZPZ128G	KBG3AZPZ256G	KBG3AZPZ512G
	KBG30ZMS128G	KBG30ZMS256G	KBG30ZMS512G
	KBG3AZMS128G	KBG3AZMS256G	KBG3AZMS512G
Interface Speed	10 GT/	/s (Gen3x2 Lane), 8 GT/s (Gen3x1 /s (Gen2x2 Lane), 5 GT/s (Gen2x1 s (Gen1x2 Lane), 2.5 GT/s (Gen1x	Lane)
Sequential Read <sup>1)</sup>	1,310 MB/s	1,415 MB/s	1,520 MB/s
(Up to)	{1,250 MiB/s}	{1,350 MiB/s}	{1,450 MiB/s}
Sequential Write <sup>1)</sup>	470 MB/s	840 MB/s	1,050 MB/s
(Up to)	{450 MiB/s}	{800 MiB/s}	{1,000 MiB/s}

Note: 1) Under the condition of measurement with 128 KiB unit sequential access and 4KiB align. Queue depth is 32, and access range is 16GiB.

1KiB (Kibibyte) =  $2^{10}$  bytes = 1024 bytes

## > SUPPLY VOLTAGE

Standard Models	M.2 1620 Single Package	M.2 2280 Module
Allowable voltage	3.3 V ±5 % 1.8 V ±5 % 1.2 V ±5 %	3.3 V ±5 %
Allowable noise/ripple	100 mV p-	p, 0-10MHz
Allowable supply rise time	Comply to the PCI-SIG specification of Power Up/Down Sequence	2 –100 ms

## > POWER CONSUMPTION

Operation	M.2 1620 Single Package				
(Ta <sup>1)</sup> =25°C)	KBG30ZPZ128G KBG3AZPZ128G	KBG30ZPZ256G KBG3AZPZ256G	KBG30ZPZ512G KBG3AZPZ512G		
Read <sup>2)</sup>	2.7 W typ.	2.8 W typ.	2.8 W typ.		
Write <sup>2)</sup>	2.1 W typ.	2.4 W typ.	2.8 W typ.		
Power State3 <sup>3)</sup>		50 mW typ.			
Power State4 <sup>3)</sup>		5 mW typ.			

Operation	M.2 2230 Module				
(Ta <sup>1)</sup> =25°C)	KBG30ZMS128G KBG3AZMS128G	KBG30ZMS256G KBG3AZMS256G	KBG30ZMS512G KBG3AZMS512G		
Read <sup>2)</sup>	3.2 W typ.	3.3 W typ.	3.3 W typ.		
Write <sup>2)</sup>	2.5 W typ.	2.8 W typ.	3.2 W typ.		
Power State 3 <sup>3)</sup>		50 mW typ.			
Power State 4 <sup>3)</sup>		5 mW typ.			

Note: 1) Ambient Temperature

2) The values are specified at the condition causing maximum power consumption and Power State 0.

3) PCIe Link state L1.2

Power consumption during the Admin command processing is excluded.



# **ENVIRONMENTAL CONDITIONS**

### **TEMPERATURE**

0	Rai	Oue disust	
Condition	M.2 1620 Single Package	M.2 2280 Module	Gradient
Operating <sup>1)</sup>	0 °C (Tc) – 80 °C (Tc) (Package Temperature)	0 °C (Tc) – 80 °C (Tc) (Components Temperature)	30 °C (Ta) / h maximum
Non-operating	-40 °C	30 °C / h maximum	
Under Shipment <sup>2)</sup>	-40 °C	30 °C / h maximum	

Note: 1) Ta: Ambient Temperature, Tc: Package Surface or Components Temperature

2) Packaged in Toshiba Memory Corporation's original shipping package.

## > HUMIDITY

Range		
8 % – 90 % R.H. (No condensation)		
8 % – 95 % R.H. (No condensation)		
5 % – 95 % R.H.		
32.5 °C (Operating) 40.0 °C (Non-operating / Shipping)		

Note: 1) Packaged in Toshiba Memory Corporation's original shipping package.

## > SHOCK

Condition	Range			
Operating <sup>1)</sup>	14.709 km/s <sup>2</sup> {1,500 G}, 0.5 ms half sine wave			
Non-operating <sup>1)</sup>	14.709 KH/S {1,500 G}, 0.5 HIS Hall Sille Wave			
Under Shipment <sup>2)</sup>	100 cm free drop			

Note: 1) Apply shocks in each direction of the drive's three mutually perpendicular axes, one axis at a time. 2) Packaged in Toshiba Memory Corporation's original shipping package.

### **VIBRATION**

Condition	Range
Operating	196 m/s² {20 G} Peak, 10 - 2,000 Hz
Non-operating	(20 minutes per axis) x 3 axis

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## COMPLIANCE

### > SAFETY / EMI STANDARDS

Title	Description	Region
UL <sup>1)</sup> (Underwriters Laboratories)	UL 60950-1	USA <sup>2)</sup>
cUL <sup>1)</sup> (Underwriters Laboratories of Canada)	CSA-C22.2 No.60950-1-07	Canada
TÜV <sup>1)</sup> (Technischer Überwachungs Verein)	EN 60950-1	EURO
KC <sup>1)</sup>	KN32, KN35	Korea
FCC <sup>1)</sup>	FCC part 15 Subpart B	USA
BSMI <sup>1)</sup> (Bureau of Standards, Metrology and Inspection)	CNS13438 (CISPR Pub. 22)	Taiwan
CE <sup>1)</sup>	EN 55032, EN 55024	EURO
RCM <sup>1)</sup>	AS/NZS CISPR 32	Australia, New Zealand
ISED <sup>1)</sup>	ICES-003	Canada
Moroccan conformity mark <sup>1)</sup>	NM EN 55032, NM EN 22024	Morocco
VCCI <sup>1)</sup>	VCCI-CISPR32	Japan

Note: 1) The Safety/EMI Standard is supported for KBG3xZMSxxxx only.

2) UL certification is basically on a voluntary basis.

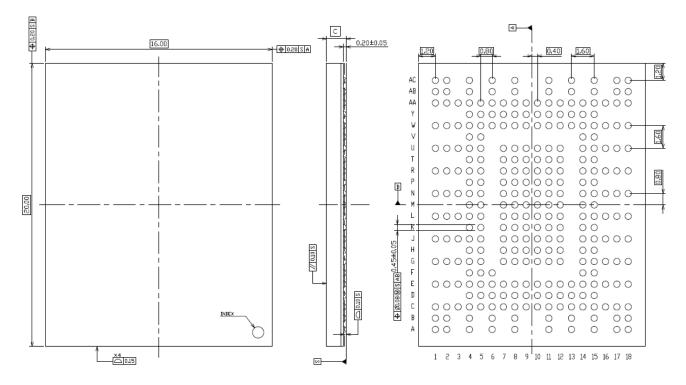
## > RELIABILITY

Parameter	Value
Mean Time to Failure	1,500,000 hours
Product Life	Approximately 5 years

# **MECHANICAL SPECIFICATIONS**

### > M.2 1620 SINGLE PACKAGE

Model Number	Weight	Width	Height	Length
KBG30ZPZ128G				
KBG3AZPZ128G	0.85 g typ.		1.30 mm	
KBG30ZPZ256G	0.05 g typ.	16.00 mm	1.50 mm	20.00 mm
KBG3AZPZ256G		10.00 11111		20.00 11111
KBG30ZPZ512G	1.00 g tvp		1.50 mm	
KBG3AZPZ512G	1.00 g typ.		1.50 11111	



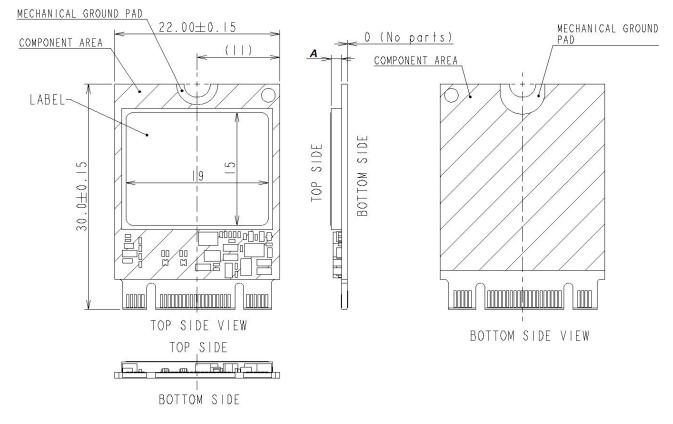
#### Unit:mm

Dimension	Description	KBG30ZPZ128G KBG3AZPZ128G KBG30ZPZ256G KBG3AZPZ256G	KBG30ZPZ512G KBG3AZPZ512G
С	Thickness of BGA Package	1.30 mm Max.	1.50 mm Max.

### Figure 1: Dimensions of KBG3xZPZxxxx (Single Package)

## > M.2 2230 MODULE

Model Number	Weight	Width	Height	Length
KBG30ZMS128G				
KBG3AZMS128G	2.42 g typ.		2.18 mm	
KBG30ZMS256G	0 71	22.00 mm	2.1011111	30.00 mm
KBG3AZMS256G		22.00 11111		30.00 mm
KBG30ZMS512G	2.60 g typ.		2.38 mm	
KBG3AZMS512G	2.00 g typ.		2.50 11111	



#### Unit:mm

Dimension	Description	KBG30ZMS128G KBG3AZMS128G KBG30ZMS256G KBG3AZMS256G	KBG30ZMS512G KBG3AZMS512G
А	Thickness of BGA Package (without label)	1.30 mm Max.	1.50 mm Max.

### Figure 2: Dimensions of KBG3xZMSxxxx (M.2 2230 Module)

### INTERFACE CONNECTOR

### M.2 1620 SINGLE PACKAGE

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18
Α	DNU	DNU		DNU		DNU		DNU			DNU		DNU		DNU		DNU	DNU
В	DNU	DNU		DNU		NC		DNU			DNU		DNU		DNU		DNU	DNU
С	GND	GND	GND	GND	GND	DNU	NC	NC	DNU	NC	DNU	DNU	RFU	RFU	GND	DNU	DNU	DNU
D				REF CLKP	REF CLKN	GND	PER ST#	CLK REQ#	PWR _1	PWR _1	GND	DNU	DIAG1	NC	RFU			
Е	GND	GND	GND	GND	GND	GND	GND	NC	PWR _1	PWR _1	GND	NC	DIAG0	GND	GND	DNU	DNU	DNU
F				PERp0	PERn0	GND								PE DET	RFU			
G	GND	GND	GND	GND	GND		PWR 3	PWR 3	GND	GND	PWR 3	PWR 3		GND	GND	DNU	DNU	DNU
Н				PETp0	PETn0		PWR 3	PWR 3	GND	GND	PWR 3	PWR 3		RFU	RFU			
J	GND	GND	GND	GND	GND		PWR 3	PWR 3	GND	GND	PWR 3	PWR 3		GND	GND	DNU	DNU	DNU
Κ				PERp1	PERn1		GND	GND	GND	GND	GND	GND		RFU	RFU			
L	GND	GND	GND	GND	GND		RFU	RFU	RFU	RFU	RFU	RFU		GND	GND	DNU	DNU	NC
Μ				PETp1	PETn1		RFU	RFU	GND	GND	RFU	RFU		RFU	RFU			
Ν	GND	GND	GND	GND	GND		RFU	RFU	RFU	RFU	RFU	RFU		GND	GND	DNU	NC	NC
Ρ				NC	NC		GND	GND	GND	GND	GND	GND		RFU	RFU			
R	GND	GND	GND	GND	GND		PWR _2	PWR _2	GND	GND	PWR _2	PWR _2		GND	GND	DNU	NC	NC
Т				NC	NC		PWR _2	PWR _2	GND	GND	PWR _2	PWR _2		RFU	RFU			
U	GND	GND	GND	GND	GND		PWR _2	PWR _2	GND	GND	PWR _2	PWR _2		GND	GND	DNU	NC	NC
V				NC	NC									RFU	RFU			
W	GND	GND	GND	GND	GND	GND	LED 1#	RFU	PWR _1	PWR _1	GND	RFU	RFU	GND	GND	DNU	DNU	NC
Y				NC	NC	GND	DNU	DNU	PWR _1	PWR _1	GND	DNU	GND	DNU	DNU			
AA	GND	GND	GND	GND	GND	DNU	DNU	DNU	DNU	NC	DNU	DNU	DNU	GND	GND	DNU	DNU	DNU
AB	DNU	DNU		DNU		DNU		DNU			DNU		DNU		DNU		DNU	DNU
AC	DNU	DNU		DNU		DNU		DNU			DNU		DNU		DNU		DNU	DNU

Note: 1) The total ball number is 291.

2) The voltage powers must be supplied to each ball on all power rails.

3) NC is not used in KBG3xZPZxxxx. But NC ball function is assigned in PCI-SiG specification.

 NC, DNU and RFU must be connected to independent OPEN land, and can't be connected between each other on host board.

5) DIAG0 and DIAG1 are engineering diagnosis balls. Toshiba Memory Corporation requests to enable access to DIAG0 and DIAG1 on host board.

### Figure 3: Ball Map of KBG3xZPZxxxx (Single Package)



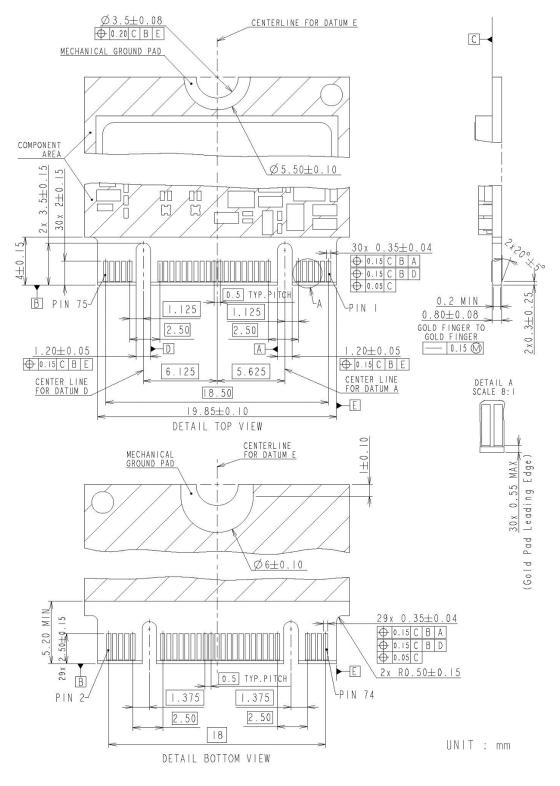
### > SINGLE PACKAGE INTERFACE SIGNALS

Interface	Signal Name	Description	Location			
	PWR_1	3.3 V Source	D9, D10, E9, E10, W9, W10, Y9, Y10			
Power and Grounds	PWR_2	1.8 V Source	R7, R8, R11, R12, T7, T8, T11, T12, U7, U8, U11, U12			
	PWR_3	1.2 V Source	G7, G8, G11, G12, H7, H8, H11, H12, J7, J8, J11, J12			
Power and Grounds	GND	GND	C1-C5, C15, D6, D11, E1-E7, E11, E14, E15, F6, G1- G5, G9, G10, G14, G15, H9, H10, J1-J5, J9, J10, J14, J15, K7-K12, L1-L5, L14, L15, M9, M10, N1- N5, N14, N15, P7-P12, R1-R5, R9, R10, R14, R15, T9, T10, U1-U5, U9, U10, U14, U15, W1- W6, W11, W14, W15, Y6, Y11, Y13, AA1-AA5, AA14, AA15			
	PERp0, PERn0	PCIe 0 Device Receiver	F4, F5			
	PETp0, PETn0	PCIe 0 Device Transfer	H4, H5			
	PERp1, PERn1	PCIe 1 Device Receiver	K4, K5			
PCIe	PETp1, PETn1	PCle 1 Device Transfer	M4, M5			
	REFCLKp, REFCLKn	PCIe Reference Clock	D4, D5			
	PERST#	PE-Reset	D7			
	CLKREQ#	Clock Request	D8			
SSD Specific	LED1#	Device Activity	W7			
Signals	PEDET	Host I/F Indication (PCIe:OPEN / SATA:GND)	F14			
Optional Signals	DIAG0, DIAG1	Diagnosis, option for engineering	D13, E13			

Interface	Signal Name	Description	Location
	RFU	Reserved; OPEN	C13, C14, D15, F15, H14, H15, K14, K15, L7, L8, L9, L10, L11, L12, M7, M8, M11, M12, M14, M15, N7, N8, N9, N10, N11, N12, P14, P15, T14, T15, V14, V15, W8, W12, W13
Other Signals	DNU	Manufacturing purpose only;OPEN	A1, A2, A4, A6, A8, A11, A13, A15, A17, A18, B1, B2, B4, B8, B11, B13, B15, B17, B18, C6, C9, C11, C12, C16-C18, D12, E16- E18, G16-G18, J16-J18, L16, L17, N16, R16, U16, W16, W17, Y7, Y8, Y12, Y14, Y15, AA6-AA9, AA11-AA13, AA16-AA18, AB1, AB2, AB4, AB6, AB8, AB11, AB13, AB15, AB17, AB18, AC1, AC2, AC4, AC6, AC8, AC11, AC13, AC15, AC17, AC18
	NC	Not used; OPEN	B6, C7, C8, C10, D14, E8, E12, L18, N17, N18, P4, P5, R17, R18, T4, T5, U17, U18, V4, V5, W18, Y4, Y5, AA10



## > M.2 2230 MODULE



Unit:mm



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### > M.2 2230 MODULE CONNECTOR PIN ASSIGNMENT

Pin #	Signal Name	Description	Pin #	Name	Description
1	CONFIG_3	GND	2	+3.3V	3.3 V Source
3	GND	GND	4	+3.3V	3.3 V Source
5	Reserved	NC	6	Reserved	NC
7	Reserved	NC	8	Reserved	NC
9	Reserved	NC	10	LED1#	Device Activity
11	Reserved	NC	Nistala		
			Notch		
Notch			20	Reserved	NC
21	CONFIG_0	GND	22	Reserved	NC
23	Reserved	NC	24	Reserved	NC
25	Reserved	NC	26	Reserved	NC
27	GND	GND	28	Reserved	NC
29	PETn1	PCle 1	30	Reserved	NC
31	PETp1	Device Transfer	32	Reserved	NC
33	GND	GND	34	Reserved	NC
35	PERn1	PCle 1	36	Reserved	NC
37	PERp1	Device Receiver	38	Reserved	NC
39	GND	GND	40	Reserved	NC
41	PETn0	PCle 0	42	Reserved	NC
43	PETp0	Device Transfer	44	Reserved	NC
45	GND	GND	46	Reserved	NC
47	PERn0	PCle 0	48	Reserved	NC
49	PERp0	Device Receiver	50	PERST#	PE-Reset
51	GND	GND	52	CLKREQ#	Clock Request
53	REFCLKn	PCIe Reference Clock	54	PEWAKE#	NC
55	REFCLKp	PCIe Reference Clock	56	MFG DATA	
57	GND	GND	58	MFG CLOCK	Manufacturing pin. Must <b>NOT</b> be connected on host board.
Notch			Notch		
67	Reserved	NC	68	SUSCLK	NC
69	PEDET	Host I/F Indication (PCIe:OPEN / SATA:GND)	70	+3.3V	3.3 V Source
71	GND	GND	72	+3.3V	3.3 V Source
73	GND	GND	74	+3.3V	3.3 V Source
75	GND	GND			
		1			



## **COMMAND TABLE**

#### **ADMIN Command set**

Op-Code	Command Name
00h	Delete I/O Submission Queue
01h	Create I/O Submission Queue
02h	Get Log Page
04h	Delete I/O Completion Queue
05h	Create I/O Completion Queue
06h	Identify
08h	Abort
09h	Set Features
0Ah	Get Features
0Ch	Asynchronous Event Request
10h	Firmware Commit
11h	Firmware Image Download
14h	Device Self-Test (DST)
80h	Format NVM
81h	Security Send
82h	Security Receive

### Set Features / Get Features Set

Op-Code	Feature Name
01h	Arbitration
02h	Power Management
04h	Temperature Threshold
05h	Error Recovery
06h	Volatile Write Cache
07h	Number of Queues
08h	Interrupt Coalescing
09h	Interrupt Vector Configuration
0Ah	Write Atomicity
0Bh	Asynchronous Event Configuration
0Ch	Autonomous Power State Transition
0Dh	Host Memory Buffer (HMB)
10h	Host Controlled Thermal Management (HCTM)

#### NVMe Command Set

Op-Code	Command Name
00h	Flush
01h	Write
02h	Read
04h	Write Uncorrectable
05h	Compare
09h	Dataset Management

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